SIEMENS

IL211A/212A/213A

PHOTOTRANSISTOR SMALL OUTLINE SURFACE MOUNT OPTOCOUPLER

NEW

FEATURES

- **High Current Transfer Ratio**
  IL211A—20% Minimum
  IL212A—50% Minimum
  IL213A—100% Minimum
- **Isolation Voltage, 2500 VAC_{RMS}**
- **Electrical Specifications Similar to Standard 6 Pin Coupler**
- **Industry Standard SOIC-8 Surface Mountable Package**
- **Standard Lead Spacing, .05"**
- **Available in Tape and Reel Option (Conforms to EIA Standard RS481A)**
- **Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering**
- **Underwriters Lab File #E52744 (Code Letter P)**

DESCRIPTION

The IL211A/212A/213A are optically coupled pairs with a Gallium Arsenide infrared LED and a silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output. The IL211A//212A/213A comes in a standard SOIC-8 small outline package for surface mounting which makes it ideally suited for high density applications with limited space. In addition to eliminating through-holes requirements, this package conforms to standards for surface mounted devices.

A choice of 20, 50, and 100% minimum CTR at I_F=10 mA makes these optocouplers suitable for a variety of different applications.

Maximum Ratings

Emitter

Peak Reverse Voltage .....6.0 V
Continuous Forward Current .....60 mA
Power Dissipation at 25°C.....90 mW
Derate Linearly from 25°C.....1.2 mW/°C

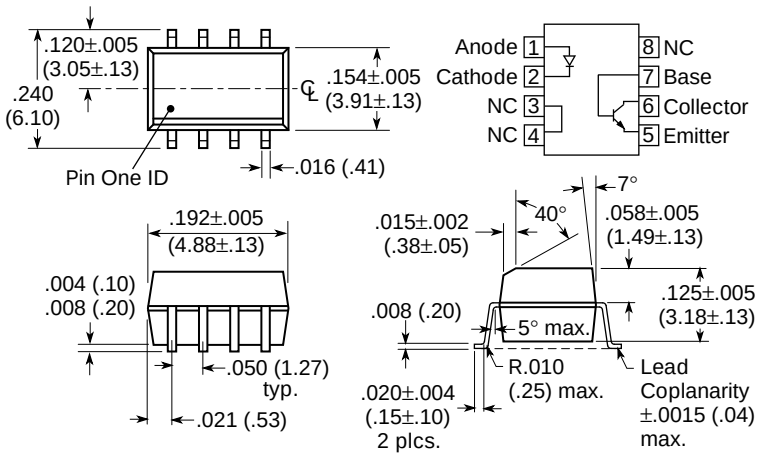
Detector

Collector-Emitter Breakdown Voltage.....30 V
Emitter-Collector Breakdown Voltage.....7 V
Collector-Base Breakdown Voltage.....70 V
Power Dissipation .....150 mW
Derate Linearly from 25°C2.0 mW/°C

Package

Total Package Dissipation at 25°C Ambient (LED + Detector) .....280 mW
Derate Linearly from 25°C.....3.3 mW/°C
Storage Temperature .....–55°C to +150°C
Operating Temperature .....–55°C to +100°C
Soldering Time at 260°C ..... 10 sec.

Dimensions in inches (mm)



Characteristics (T_A=25°C)

	Symbol	Min.	Typ.	Max.	Unit	Condition
Emitter						
Forward Voltage	V_F		1.3	1.5	V	I_F=10 mA
Reverse Current	I_R		0.1	100	µA	V_R=6.0 V
Capacitance	C_O		25		pF	V_R=0
Detector						
Breakdown Voltage	B_{VCEO} B_{VECO}		30 7		V V	I_C=10 µA I_E=10 µA
Dark Current, Collector-Emitter	$I_{CEOdark}$		5	50	nA	V_{CE}=10 V I_F=0
Capacitance, Collector-Emitter	C_{CE}		10		pF	V_{CE}=0
Package						
DC Current Transfer Ratio IL211A IL212A IL213A	CTR_{DC}	 20 50 100	 50 80 130		%	I_F=10 mA, V_{CE}=5 V
Saturation Voltage, Collector-Emitter	V_{CEsat}			0.4		I_F=10 mA, I_C=2.0 mA
Isolation Test Voltage	V_{IO}	2500			VAC_{RMS}	
Capacitance, Input toOutput	C_{IO}		0.5		pF	
Resistance, Input to Output	R_{IO}		100		GΩ	
Switching Time	t_{on},t_{off}		3.0		µs	I_C=2 mA, R_E=100 Ω, V_{CE}=10 V

Figure 1. Forward voltage versus forward current

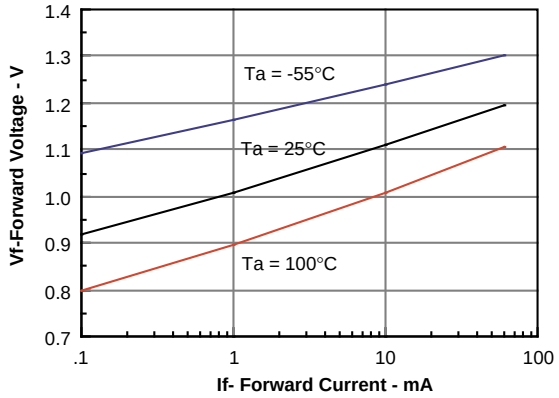


Figure 2. Normalized non-saturated and saturated CTRce versus LED current

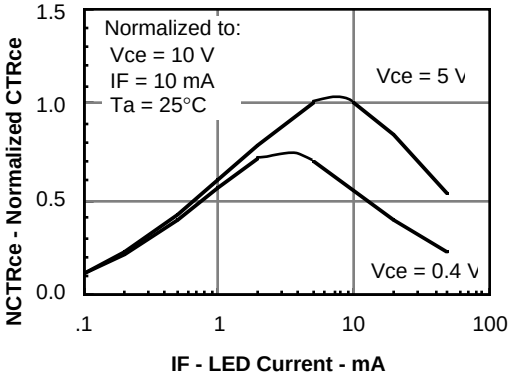


Figure 3. Collector-emitter current versus LED current

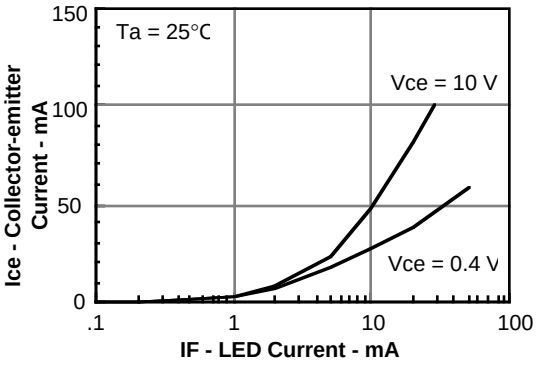


Figure 4. Normalized collector-base photocurrent versus LED current

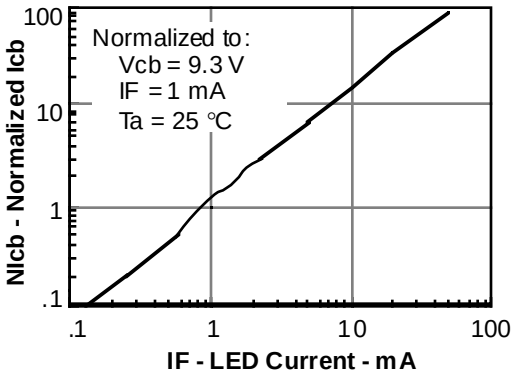


Figure 5. Normalized collector-base photocurrent versus LED current

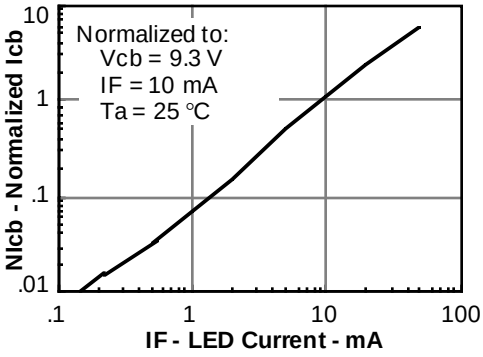


Figure 6. Collector-base photocurrent versus LED current

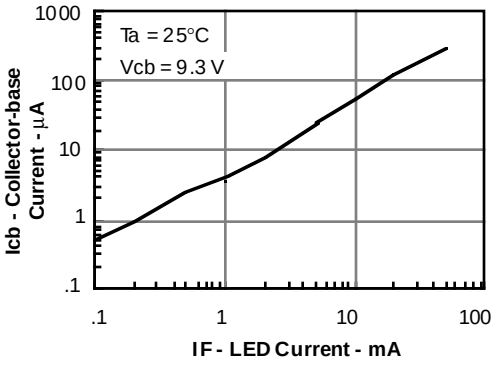


Figure 7. Collector-emitter leakage current versus temperature

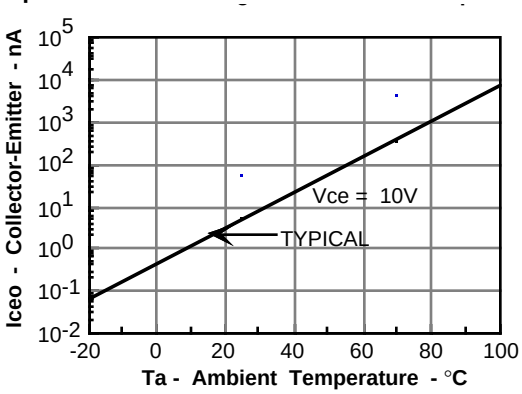


Figure 8. Normalized saturated HFE versus base current and temperature

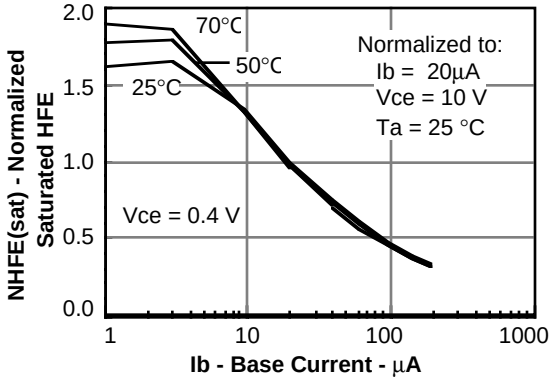


Figure 9. Typical switching characteristics versus base resistance (saturated operation)

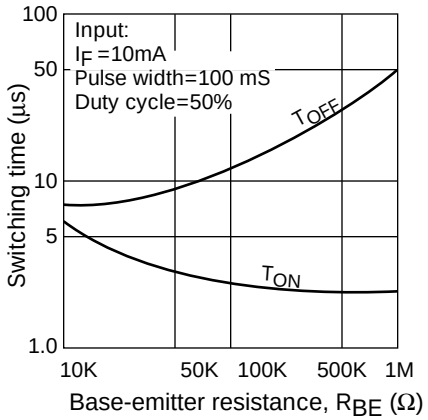


Figure 10. Typical switching times versus load resistance